

L Number	Hits	Search Text	DB	Time stamp
1	281	257/68	USPAT	2004/05/26 11:17
2	826	257/288	USPAT	2004/05/26 11:17
3	3238	257/296	USPAT	2004/05/26 11:17
4	1313	257/314	USPAT	2004/05/26 11:17
5	2308	257/315	USPAT	2004/05/26 11:17
6	550	257/377	USPAT	2004/05/26 11:17
7	402	257/380	USPAT	2004/05/26 11:17
8	1041	257/382	USPAT	2004/05/26 11:17
9	1171	257/412	USPAT	2004/05/26 11:18
10	649	257/413	USPAT	2004/05/26 11:18
-	1	10/064383	USPAT	2004/05/26 10:20
-	1		USPAT	2004/05/26 10:28
-	1		USPAT	2004/05/26 10:11
-	1		USPAT	2004/05/26 10:11
-	1		USPAT	2004/05/26 10:11
-	0	(electron adj capturing) and memory and device and width and conductive and tunnel and oxide and spacer and sidewall and gate and dielectric and nitride and silicon and polysilicon	USPAT	2004/05/26 10:23
-	194	electron and memory and device and width and conductive and tunnel and oxide and spacer and sidewall and gate and dielectric and nitride and silicon and polysilicon	USPAT	2004/05/26 10:23
-	0	electron and memory and device and width and conductive and tunnel and oxide and spacer and sidewall and gate and dielectric and nitride and silicon and polysilicon and (electron-capturing adj layer)	USPAT	2004/05/26 10:24
-	5	electron and memory and device and width and conductive and tunnel and oxide and spacer and sidewall and gate and dielectric and nitride and silicon and polysilicon and (memory adj device adj structure)	USPAT	2004/05/26 10:24
-	1	"6455362".PN. and (memory or device or structure or electron or capturing or tunnel or oxide or nitride or silicon or polysilicon or spacer or sidewall or conductive or gate or dielectric or width or metal)	USPAT	2004/05/26 10:31
-	1	"5950088".PN. and (memory or device or structure or electron or capturing or tunnel or oxide or nitride or silicon or polysilicon or spacer or sidewall or conductive or gate or dielectric or width or metal)	USPAT	2004/05/26 10:32
-	1	"5643812".PN. and (memory or device or structure or electron or capturing or tunnel or oxide or nitride or silicon or polysilicon or spacer or sidewall or conductive or gate or dielectric or width or metal)	USPAT	2004/05/26 10:32
-	1	"5585293".PN. and (memory or device or structure or electron or capturing or tunnel or oxide or nitride or silicon or polysilicon or spacer or sidewall or conductive or gate or dielectric or width or metal)	USPAT	2004/05/26 11:16

5/26/04